ABSTRACT OF THE DISCLOSURE

The invention provides an electrostatic capacitance detection device. The electrostatic capacitance detection device can be formed of M individual power supply lines, N individual output lines, arranged in a matrix of M rows × N columns, and electrostatic capacitance detection elements provided on the crossing points of the individual power supply lines and the individual output lines, each of the electrostatic capacitance detection elements is formed of a signal detection element and a signal amplification element, the signal detection element is formed of a capacitance detecting electrode and a capacitance detecting dielectric layer, the signal amplification element formed of a metal-insulator-semiconductor (MIS) type thin film semiconductor device for signal amplification, including a gate electrode, a gate insulating layer and a semiconductor layer.